MSKSEMI















ESD

TVS

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SOD-923



Feature

80W peak pulse power per line ($t_P = 8/20\mu s$)

SOD-923 package

Replacement for MLV(0402)

Bidirectional configurations

Response time is typically < 1ns

Low clamping voltage

RoHS compliant

Transient protection for data lines to

EC61000-4-2(ESD) ±30KV(air), ±30KV(contact);

IEC61000-4-4 (EFT) 40A (5/50ns)

Applications

Cellular phones

Portable devices

Digital cameras

Power supplies

Mechanical Characteristics

Lead finish:100% matte Sn(Tin)

Mounting position: Any

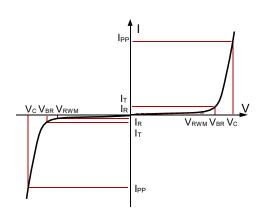
Device meets MSL 1 requirements

Pure tin plating: 7 ~ 17 um

Pin flatness:≤3mil

Electronics Parameter

| Symbol | Parameter | | |
|-----------------|--|--|--|
| V_{RWM} | Peak Reverse Working Voltage | | |
| I _R | Reverse Leakage Current @ V _{RWM} | | |
| V_{BR} | Breakdown Voltage @ I⊤ | | |
| Ι _Τ | Test Current | | |
| I _{PP} | Maximum Reverse Peak Pulse Curren | | |
| Vc | Clamping Voltage @ I _{PP} | | |
| P _{PP} | Peak Pulse Power | | |
| CJ | Junction Capacitance | | |
| I _F | Forward Current | | |
| V _F | Forward Voltage @ I _F | | |



Electrical characteristics per line@25℃ (unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Units |
|------------------------------------|-----------------|-----------------------------|------|------|------|-------|
| Peak Reverse Working Voltage | V_{RWM} | | | | 5 | V |
| Breakdown Voltage | V_{BR} | I _t = 1mA | 5.6 | 6.7 | 7.8 | V |
| Reverse Leakage Current | I _R | V _{RWM} = 5V T=25℃ | | | 1.0 | μA |
| Maximum Reverse Peak Pulse Current | I _{PP} | | | 5 | | Α |
| Clamping Voltage | Vc | I _{PP} =1A | | | 8 | V |
| Clamping Voltage | Vc | I _{PP} =3A | | | 13 | V |
| Clamping Voltage | Vc | I _{PP} =5A | | | 15 | V |
| Junction Capacitance | C _j | V _R =0V f = 1MHz | | 12 | 15 | pF |

Absolute maximum rating@25℃

| Rating | Symbol | Value | Units |
|---|------------------|-------------|------------------------|
| Peak Pulse Power (t _p =8/20µs) | P _{pp} | 80 | W |
| Operating Temperature | TJ | -55 to +150 | $^{\circ}\!\mathrm{C}$ |
| Storage Temperature | T _{STG} | -55 to +150 | $^{\circ}\mathrm{C}$ |

Typical Characteristics

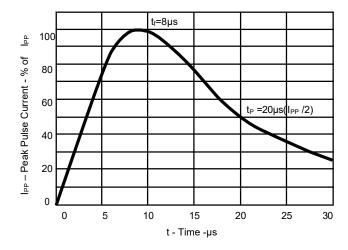


Fig 1.Pulse Waveform

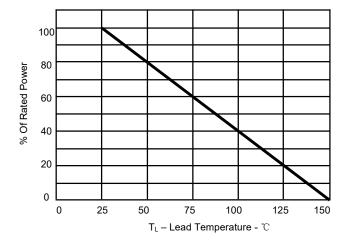


Fig 2.Power Derating Curve





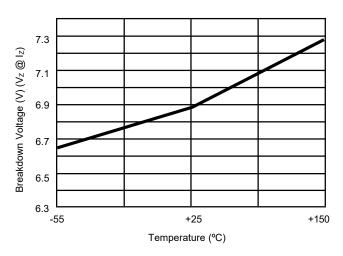


Fig 3.Typical Breakdown Voltage vs. Temperature

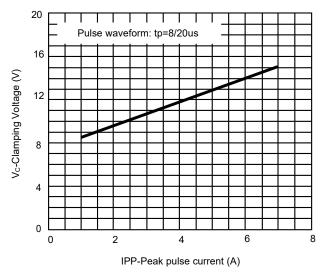


Fig 5. Clamping voltage vs. Peak pulse current

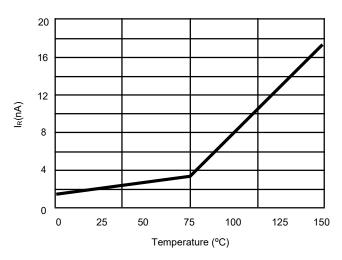


Fig 4. Typical Leakage Current vs. Temperature

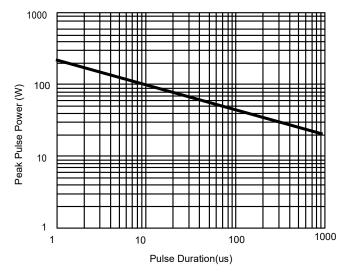
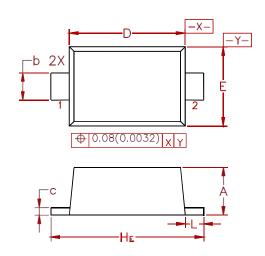


Fig 6. Non-Repetitive Peak Pulse Power vs. Pulse time

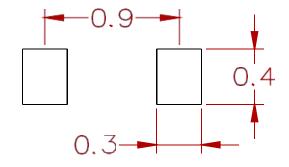


PACKAGE MECHANICAL DATA



| Dim | Millimeters | | | Inches | | | |
|-----|-------------|------|------|--------|-------|-------|--|
| | Min | Nom | Max | Min | Nom | Max | |
| Α | 0.36 | 0.40 | 0.43 | 0.014 | 0.016 | 0.017 | |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | |
| С | 0.07 | 0.12 | 0.17 | 0.003 | 0.005 | 0.007 | |
| D | 0.75 | 0.80 | 0.85 | 0.030 | 0.031 | 0.033 | |
| E | 0.55 | 0.60 | 0.65 | 0.022 | 0.024 | 0.026 | |
| HE | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 | |
| L | 0.05 | 0.10 | 0.15 | 0.002 | 0.004 | 0.006 | |

Suggested Pad Layout



Dimensions: Millimeters

REEL SPECIFICATION

| P/N | PKG | QTY |
|--------------|---------|------|
| ESD9X5.0ST5G | SOD-923 | 8000 |



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